

NPN SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500/495

Devices

2N5793

2N5794
2N5794U

Qualified Level

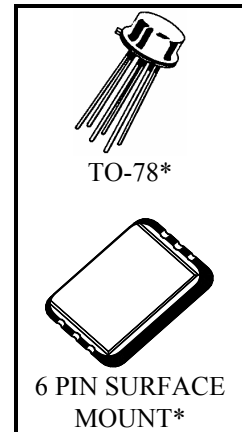
JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Symbol	Value		Units
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	75		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current	I_C	600		mAdc
		One Section⁽¹⁾	Total Device⁽²⁾	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	P_T	0.5	0.6	W
Operating & Storage Junction Temperature Range	T_{op}, T_{stg}	-65 to +200		$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$



*See MILPRF19500/495 for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Current $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	40		Vdc
Collector-Base Cutoff Current $V_{CB} = 75 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$	I_{CBO}		10 10	μAdc ηAdc
Emitter-Base Cutoff Current $V_{EB} = 6.0 \text{ Vdc}$ $V_{EB} = 4.0 \text{ Vdc}$	I_{EBO}		10 10	μAdc ηAdc

